

IN THE CLAIMS:

Please cancel Claims 1-48, without prejudice or disclaimer.

Please add the following new claims:

49. A layer of material for use in microcircuits, wherein said layer has a surface with a contour defined by the relative positions of a plurality of acceptor centers in a solid base material from which said layer is formed.

50. A layer of material as recited in claim 49, wherein said layer is formed by the steps comprising:

- (a) introducing a plurality of acceptor centers into said base material;
- (b) introducing a plurality of atoms into said base material at a location spaced apart from the location of said acceptor centers;
- (c) transporting said atoms toward said acceptor centers; and
- (d) expunging said layer from said base material in the region of said acceptor centers, whereby said expunged layer has said surface with a contour defined by said relative positions of said acceptor centers.

51. A layer of material as recited in claim 49, wherein said base material comprises a semiconductor material.

52. A layer of material as recited in claim 51, wherein said semiconductor material comprises silicon.

Conto 1 7 53. A layer of material as recited in claim 50, wherein said atoms comprise hydrogen atoms.

54. A layer of material as recited in claim 49, wherein said acceptor centers are formed by introducing a getter material into said base material.

55. A layer of material as recited in claim 54, wherein said base material comprises silicon and said getter material is selected from the group consisting of Group III materials.

56. A layer of material as recited in claim 54, wherein said base material comprises silicon and said getter material is selected from the group consisting of gallium and boron.

57. A layer of material for use in microcircuits, wherein said layer has a surface with a contour defined by the relative positions of a plurality of acceptor centers in a solid base material from which said layer is formed, wherein said layer is formed by the steps comprising:

- (a) introducing a plurality of acceptor centers into said base material;
- (b) introducing a plurality of atoms into said base material at a location spaced apart from the location of said acceptor centers;
- (c) transporting said atoms toward said acceptor centers; and

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sub B1* 7 (d) expunging said layer from said base material in the region of said acceptor centers, whereby said expunged layer has said surface with a contour defined by said relative positions of said acceptor centers.

58. A layer of material as recited in claim 57, wherein said base material comprises a semiconductor material.

*Cont'd C1* 59. A layer of material as recited in claim 58, wherein said semiconductor material comprises silicon.

60. A layer of material as recited in claim 57, wherein said atoms comprise hydrogen atoms.

61. A layer of material as recited in claim 57, wherein said acceptor centers are formed by introducing a getter material into said base material.

62. A layer of material as recited in claim 61, wherein said base material comprises silicon and said getter material is selected from the group consisting of Group III materials.

63. A layer of material as recited in claim 61, wherein said base material comprises silicon and said getter material is selected from the group consisting of gallium and boron.

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64. A layer of material for use in microcircuits, wherein said layer has a surface with a contour defined by the relative positions of a plurality of acceptor centers in a solid semiconductor material from which said layer is formed, wherein said layer is formed by the steps comprising:

- (a) introducing a plurality of acceptor centers into said semiconductor material;
- (b) introducing a plurality of atoms into said semiconductor material at a location spaced apart from the location of said acceptor centers;
- (c) transporting said atoms toward said acceptor centers; and
- (d) expunging said layer from said base material in the region of said acceptor centers, whereby said expunged layer has said surface with a contour defined by said acceptor centers.

65. A layer of material as recited in claim 64, wherein said semiconductor material comprises silicon.

66. A layer of material as recited in claim 64, wherein said atoms comprise hydrogen atoms.

67. A layer of material as recited in claim 64, wherein said acceptor centers are formed by introducing a getter material into said semiconductor material.

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68. A layer of material as recited in claim 67, wherein said semiconductor material comprises silicon and said getter material is selected from the group consisting of Group III materials.

69. A layer of material as recited in claim 67, wherein said semiconductor material comprises silicon and said getter material is selected from the group consisting of gallium and boron.

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70. A layer of material for use in microcircuits, wherein said layer has a surface with a contour defined by the relative positions of a plurality of acceptor centers in a solid silicon material from which said layer is formed, wherein said layer is formed by the steps comprising:

- (a) introducing a plurality of acceptor centers into said silicon material;
- (b) introducing a plurality of atoms into said silicon material at a location spaced apart from the location of said acceptor centers;
- (c) transporting said atoms toward said acceptor centers; and
- (d) expunging said layer from said base material in the region of said acceptor centers, whereby said expunged layer has said surface with a contour defined by said acceptor centers.

71. A layer of material as recited in claim 70, wherein said atoms comprise hydrogen atoms.

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72. A layer of material as recited in claim 70, wherein said acceptor centers are formed by introducing a getter material into said silicon material.

73. A layer of material as recited in claim 72, wherein said getter material is selected from the group consisting of Group III materials.

74. A layer of material as recited in claim 72, wherein said getter material is selected from the group consisting of gallium and boron.

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75. A base material for use in fabrication of microcircuits, wherein said base material includes a contour line along which a layer can be expunged, said contour line defined by the relative positions of a plurality of acceptor centers in said base material.

76. A material as recited in claim 75, wherein said base material is processed according to the steps comprising:

- (a) introducing a plurality of acceptor centers into said base material;
- (b) introducing a plurality of atoms into said material at a location spaced apart from the location of said acceptor centers; and
- (c) transporting said atoms toward said acceptor centers.

77. A layer of material as recited in claim 75, wherein said base material comprises a semiconductor material.

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78. A layer of material as recited in claim 77, wherein said semiconductor material comprises silicon.

79. A layer of material as recited in claim 76, wherein said atoms comprise hydrogen atoms.

80. A layer of material as recited in claim 75, wherein said acceptor centers are formed by introducing a getter material into said base material.

81. A layer of material as recited in claim 80, wherein said base material comprises silicon and said getter material is selected from the group consisting of Group III materials.

82. A layer of material as recited in claim 80, wherein said base material comprises silicon and said getter material is selected from the group consisting of gallium and boron.